

to the MEMS device 10. When pressure is exerted on tab 18, the springs 14 deform to open the clamp and allow the slider to be inserted or removed from pedestal 20 of the MEMS device 10.

Please replace the paragraph at page 4, lines 12-21 with the following paragraph (marked up version attached in Appendix):

Any time the MEMS device 10 is chipped or cracked, small amounts of silicon may contaminate the slider held in the MEMS device 10 or may contaminate the disc or other electrical components near the device MEMS 10. Furthermore, cracks in the MEMS device 10 can develop into more serious structural flaws or even breaks. To overcome the chipping and breakage problem, the present invention involves coating the MEMS device 10 with a ductile material, such as a metal, to prevent and reduce chipping and breakage. This armored coating serves to absorb the stress of repeated contact and prevents the stress from being transferred through the ductile material to the silicon crystals so that the silicon neither fractures, breaks, or chips.

Please replace the paragraph at page 5, lines 1-9 with the following paragraph (marked up version attached in Appendix):

Figures 2A-2B are simplified cross-sectional views of a wafer illustrating the process flow for providing microcomponents with a total armored coating. Shown in Figure 2A is a wafer substrate 30. In the first step of providing the wafer 30 with armored coating, a conformal coating of a seed layer 32 is deposited on the wafer substrate 30. Any suitable seed layer material may be used, such as Tantalum. In depositing the seed layer 32, it is desirable for the seed layer 32 to be very thin. Typically, the seed layer 32 is sputtered on and is about a few thousand Angstroms thick. The seed layer provides a surface onto which a ductile metal can be deposited.

Please replace the paragraph at page 5, line 27 - page 6, line 5 with the following paragraph (marked up version attached in Appendix):

The type of metal chosen as well as the method of depositing it on the wafer 30 may depend on the geometric factors of the features on the wafer 30. In particular, for a MEMS device having intricate or fine geometric features, CVD may provide the best deposition method. A CVD process is particularly suited for instances where the coating 34 must evenly coat very small areas.